Advanced PECVD-Nitride2(HF n=2.00, dep.rate=9.3nm/min)			
SiN depostion~1000A			
Step	**SiN Deposition**		
1	**Name**	**Value**	**Changeable**
	Process pressure	800	N
	RF point	30	N
	stabilization time	15	N
	step time(m)	**11**	**Y**
	step time(s)	**30**	**Y**
	2%SiH4 %He	1040	N
	N2	980	N
	NH3	17	N